

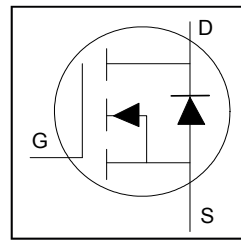
Application

- Brushed motor drive applications
- BLDC motor drive applications
- Battery powered circuits
- Half-bridge and full-bridge topologies
- Synchronous rectifier applications
- Resonant mode power supplies
- OR-ing and redundant power switches
- DC/DC and AC/DC converters
- DC/AC inverters

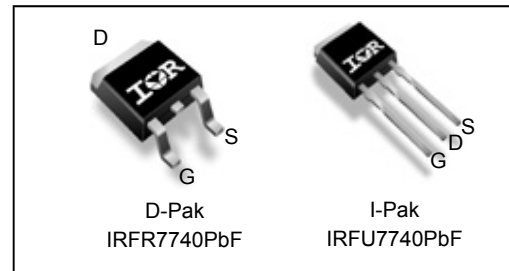
Benefits

- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche SOA
- Enhanced body diode dV/dt and dI/dt capability
- Lead-free, RoHS compliant

HEXFET® Power MOSFET



V_{DSS}	75V
R_{DS(on)} typ.	6.0mΩ
	7.2mΩ
I_D	87A



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRFR7740PbF	D-Pak	Tube	75	IRFR7740PbF
		Tape and Reel	2000	IRFR7740TRPbF
IRFU7740PbF	I-Pak	Tube	75	IRFU7740PbF

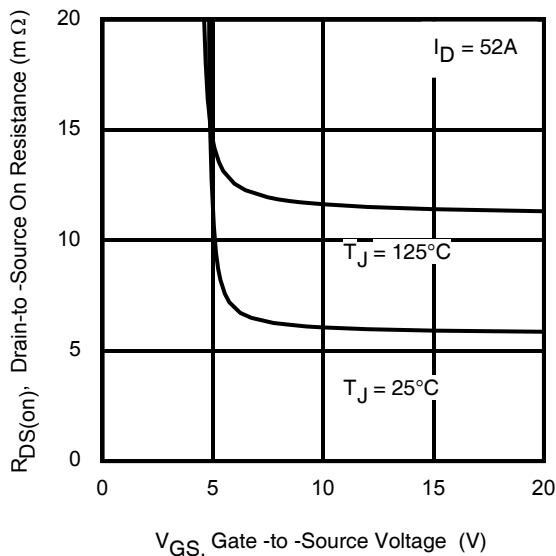


Fig 1. Typical On-Resistance vs. Gate Voltage

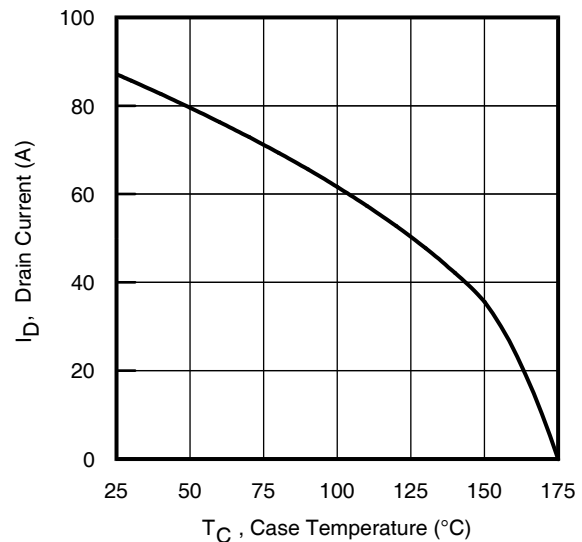


Fig 2. Maximum Drain Current vs. Case Temperature

Absolute Maximum Rating

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	87	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ (Silicon Limited)	62	
I_{DM}	Pulsed Drain Current ①	330	
$P_D @ T_C = 25^\circ\text{C}$	Maximum Power Dissipation	140	W
	Linear Derating Factor	0.95	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

Symbol	Parameter	Max.	Units
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ②	160	mJ
E_{AS} (Thermally limited)	Single Pulse Avalanche Energy ③	242	
I_{AR}	Avalanche Current ④	See Fig 15, 16, 23a, 23b	A
E_{AR}	Repetitive Avalanche Energy ⑤		mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑦	—	1.05	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	51	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	6.0	7.2	mΩ	$V_{GS} = 10\text{V}, I_D = 52\text{A}$
		—	7.0	—		$V_{GS} = 6.0\text{V}, I_D = 26\text{A}$
$V_{GS(th)}$	Gate Threshold Voltage	2.1	—	3.7	V	$V_{DS} = V_{GS}, I_D = 100\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 75\text{V}, V_{GS} = 0\text{V}$
		—	—	150		$V_{DS} = 75\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20\text{V}$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20\text{V}$
R_G	Gate Resistance	—	2.2	—	Ω	

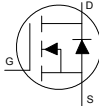
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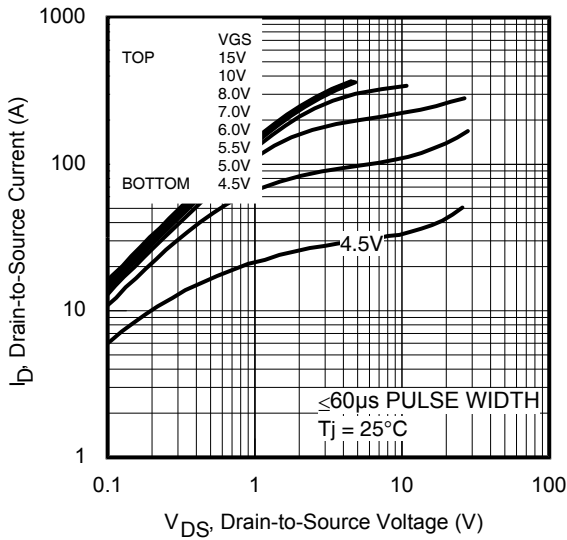
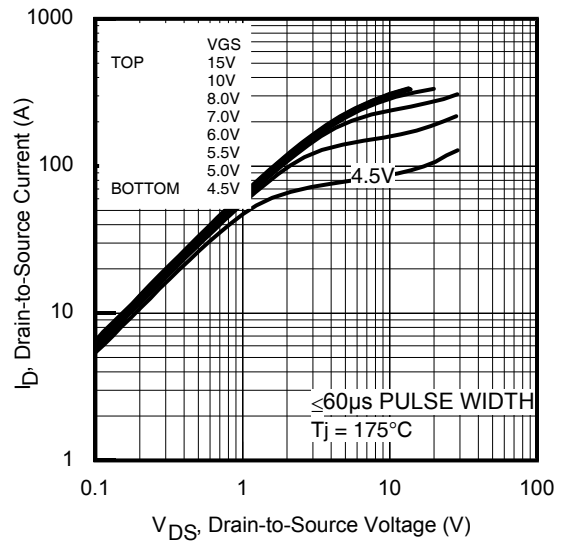
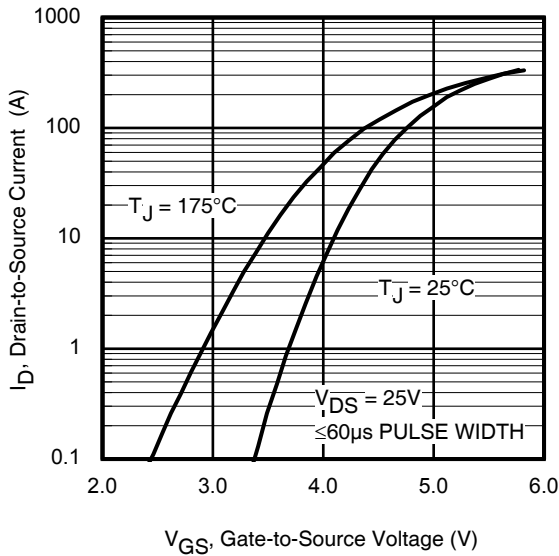
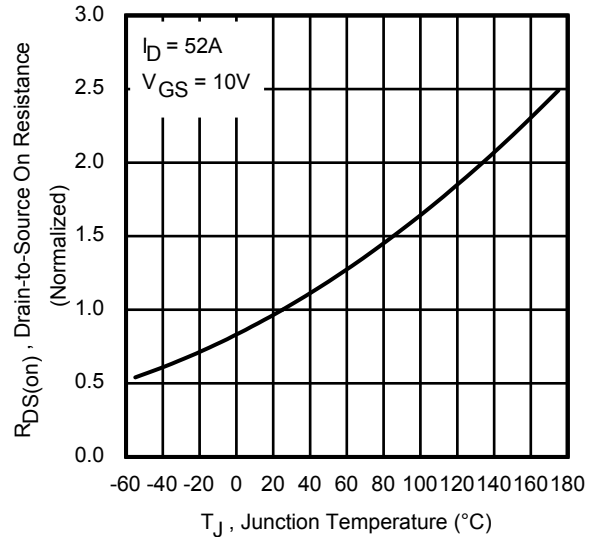
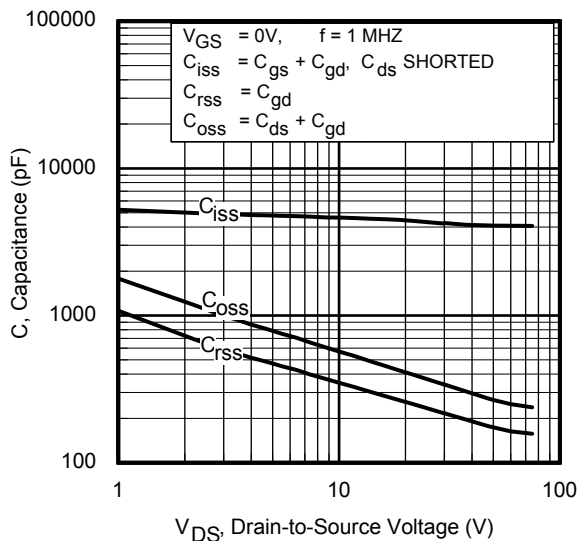
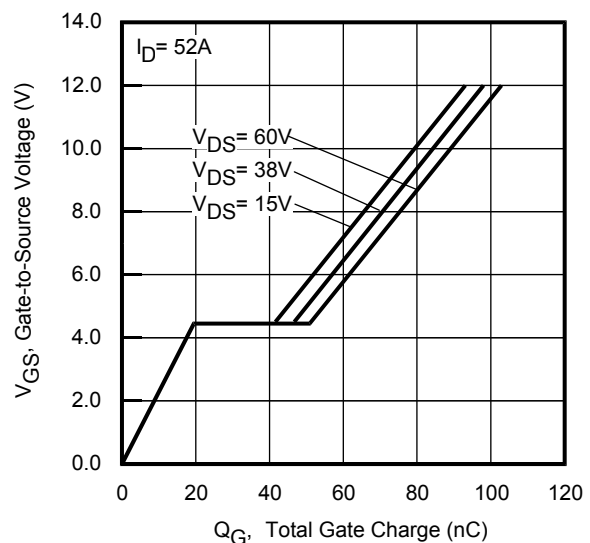
- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 120\mu\text{H}$, $R_G = 50\Omega$, $I_{AS} = 52\text{A}$, $V_{GS} = 10\text{V}$.
- ③ $I_{SD} \leq 52\text{A}$, $di/dt \leq 570\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$.
- ④ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ⑤ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑥ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
- ⑦ R_{θ} is measured at T_J approximately 90°C .
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994: <http://www.irf.com/technical-info/appnotes/an-994.pdf>
- ⑨ Limited by T_{Jmax} , starting $T_J = 25^\circ\text{C}$, $L = 1\text{mH}$, $R_G = 50\Omega$, $I_{AS} = 22\text{A}$, $V_{GS} = 10\text{V}$

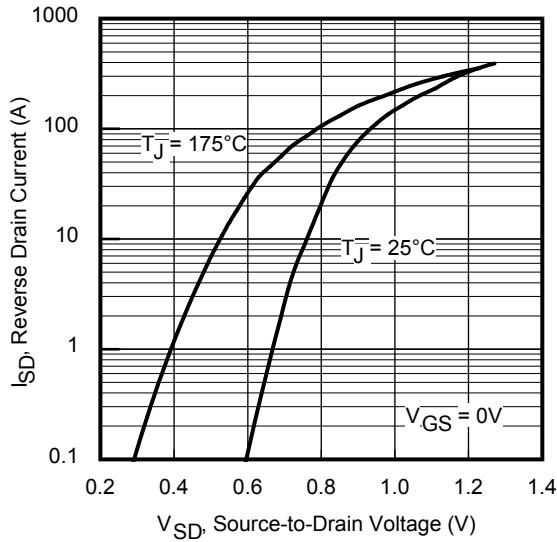
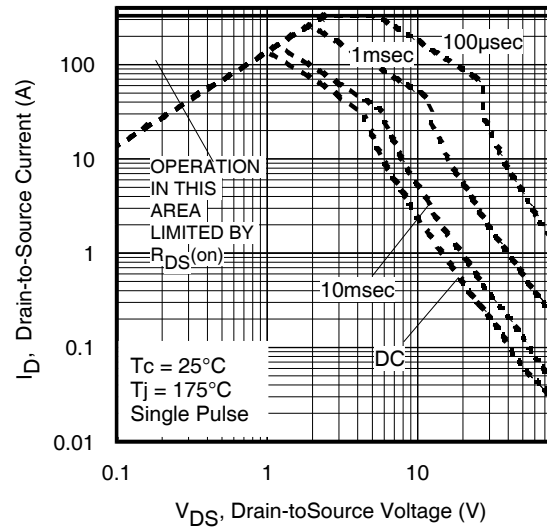
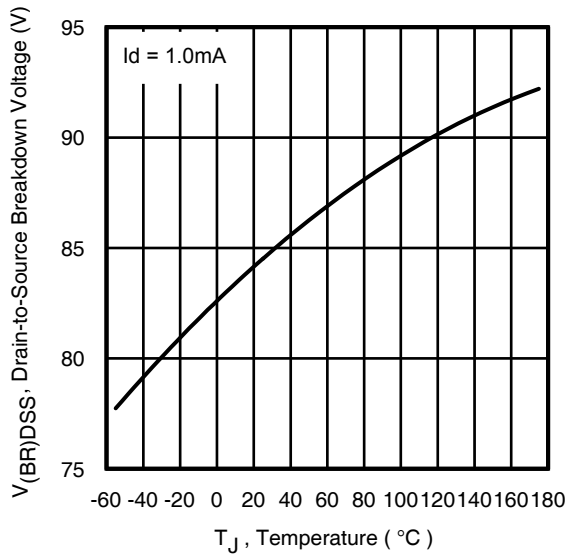
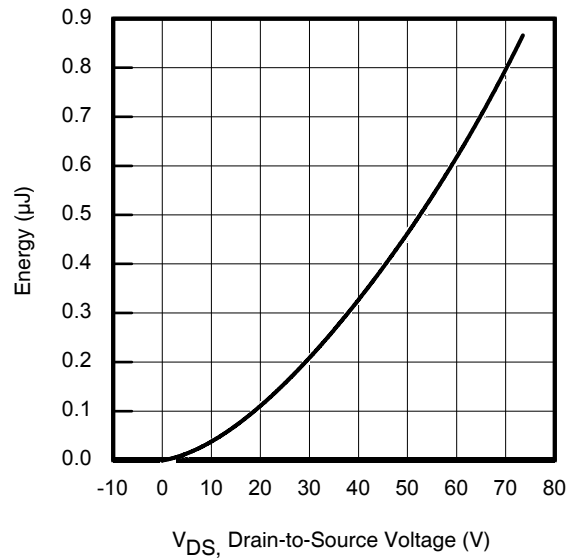
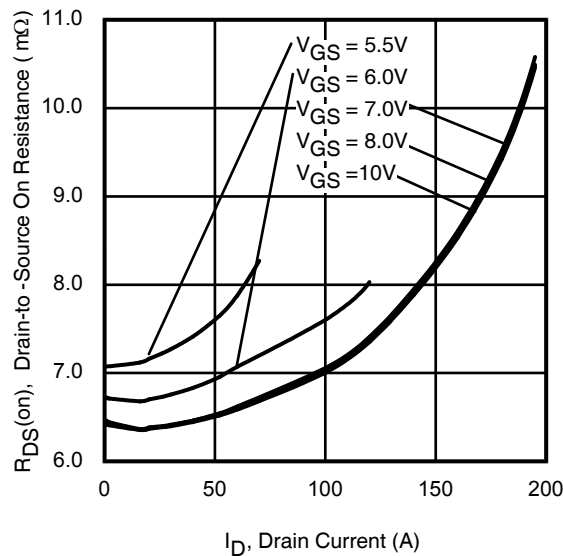
Dynamic Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

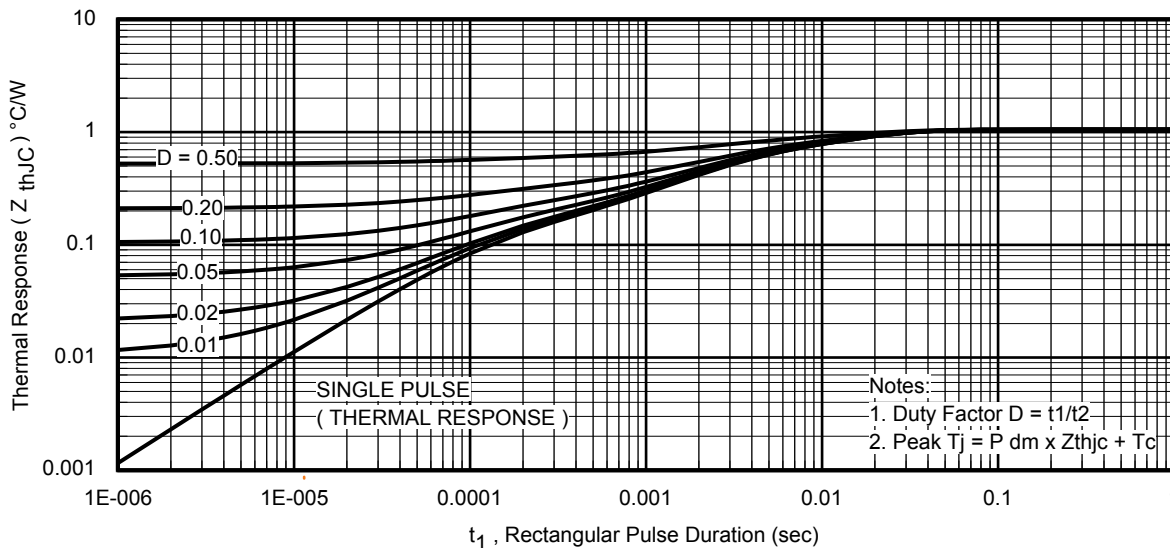
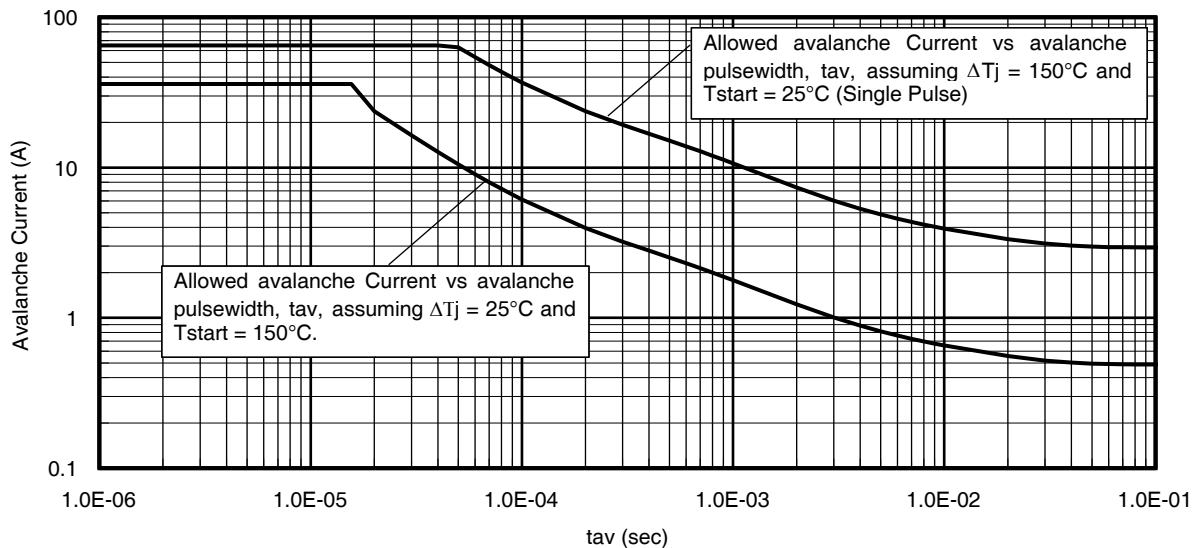
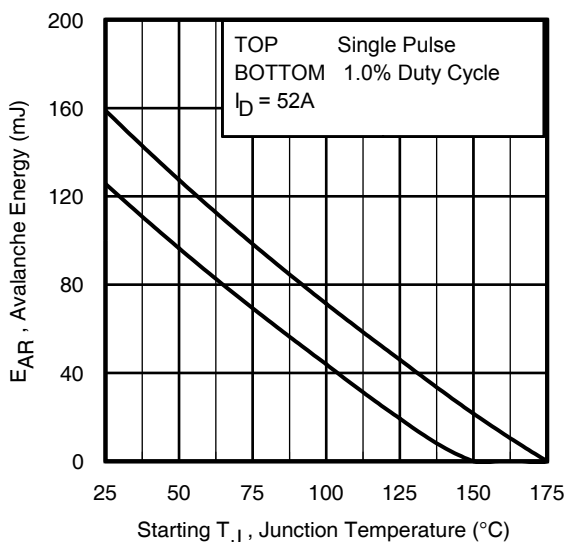
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	110	—	—	S	$V_{DS} = 25\text{V}$, $I_D = 52\text{A}$
Q_g	Total Gate Charge	—	84	126	nC	$I_D = 52\text{A}$ $V_{DS} = 38\text{V}$ $V_{GS} = 10\text{V}$ ④
Q_{gs}	Gate-to-Source Charge	—	20	—		
Q_{gd}	Gate-to-Drain Charge	—	26	—		
Q_{sync}	Total Gate Charge Sync. ($Q_g - Q_{gd}$)	—	58	—		
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 38\text{V}$ $I_D = 52\text{A}$ $R_G = 2.7\Omega$ $V_{GS} = 10\text{V}$ ④
t_r	Rise Time	—	36	—		
$t_{d(off)}$	Turn-Off Delay Time	—	55	—		
t_f	Fall Time	—	30	—		
C_{iss}	Input Capacitance	—	4430	—	pF	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1.0\text{MHz}$, See Fig.7
C_{oss}	Output Capacitance	—	370	—		
C_{riss}	Reverse Transfer Capacitance	—	230	—		
$C_{oss\ eff.(ER)}$	Effective Output Capacitance (Energy Related)	—	340	—		
$C_{oss\ eff.(TR)}$	Output Capacitance (Time Related)	—	440	—		

Diode Characteristics

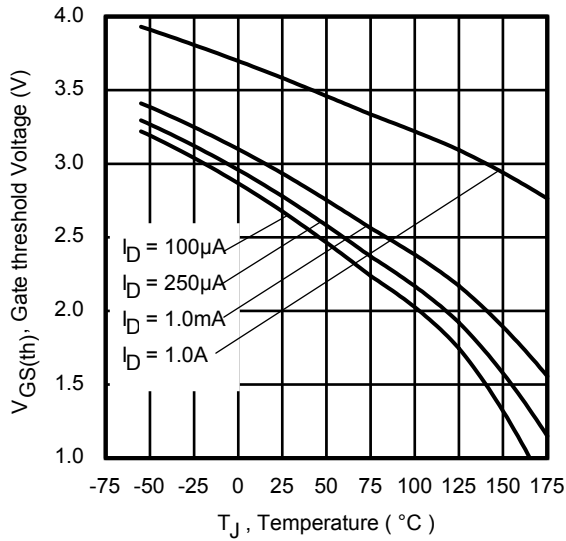
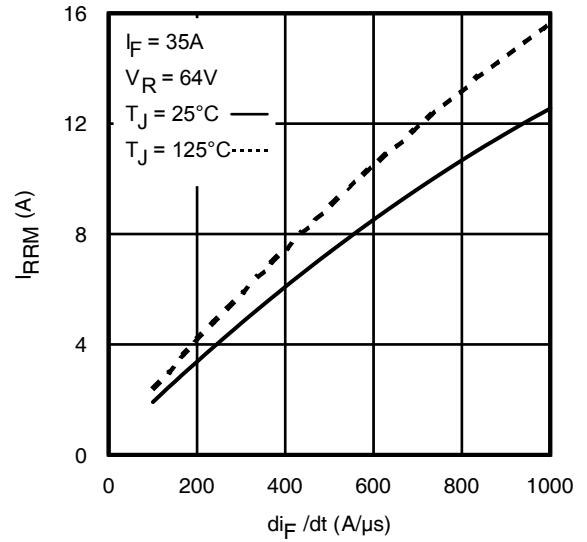
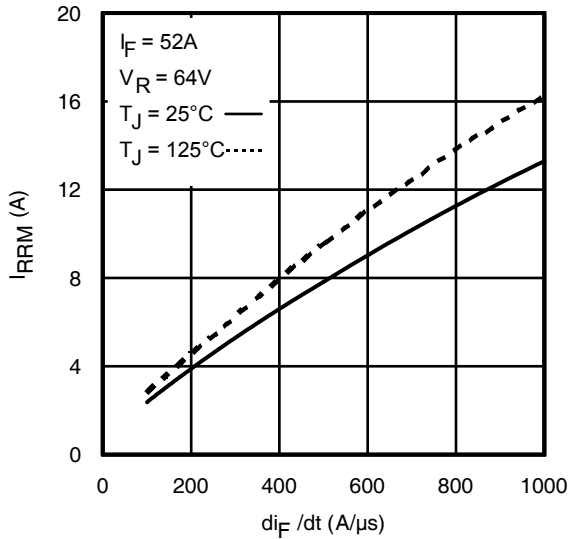
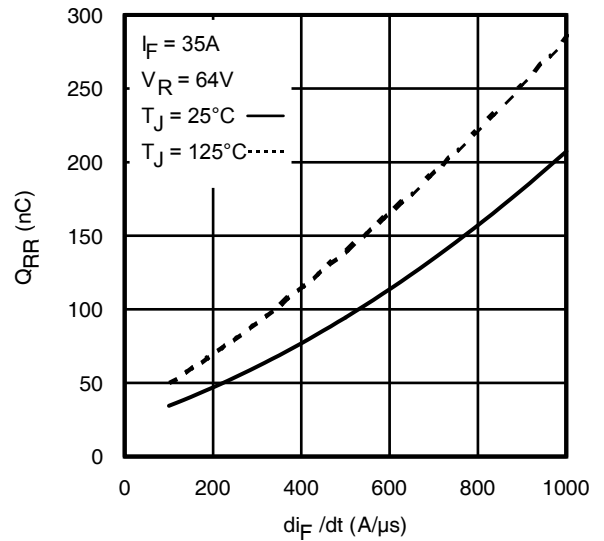
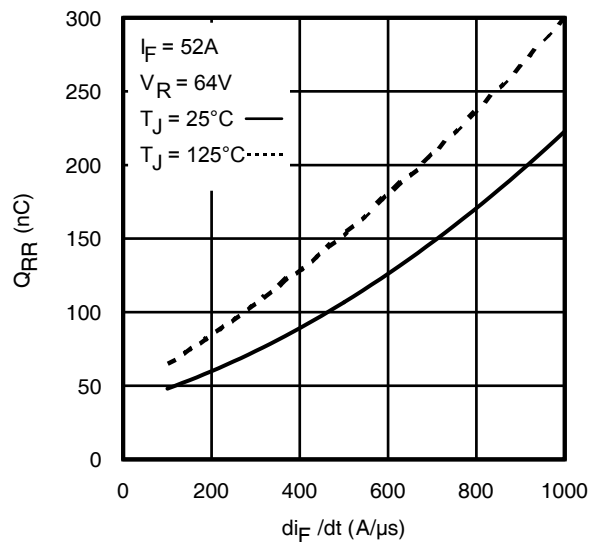
Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	87	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	330		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 52\text{A}$, $V_{GS} = 0\text{V}$ ④
dv/dt	Peak Diode Recovery dv/dt	—	12	—	V/ns	$T_J = 175^\circ\text{C}$, $I_S = 52\text{A}$, $V_{DS} = 75\text{V}$ ③
t_{rr}	Reverse Recovery Time	—	35	—	ns	$T_J = 25^\circ\text{C}$ $V_{DD} = 64\text{V}$ $T_J = 125^\circ\text{C}$ $I_F = 52\text{A}$,
		—	40	—		
Q_{rr}	Reverse Recovery Charge	—	45	—	nC	$T_J = 25^\circ\text{C}$ $di/dt = 100\text{A}/\mu\text{s}$ ④ $T_J = 125^\circ\text{C}$
		—	61	—		
I_{RRM}	Reverse Recovery Current	—	2.3	—	A	$T_J = 25^\circ\text{C}$

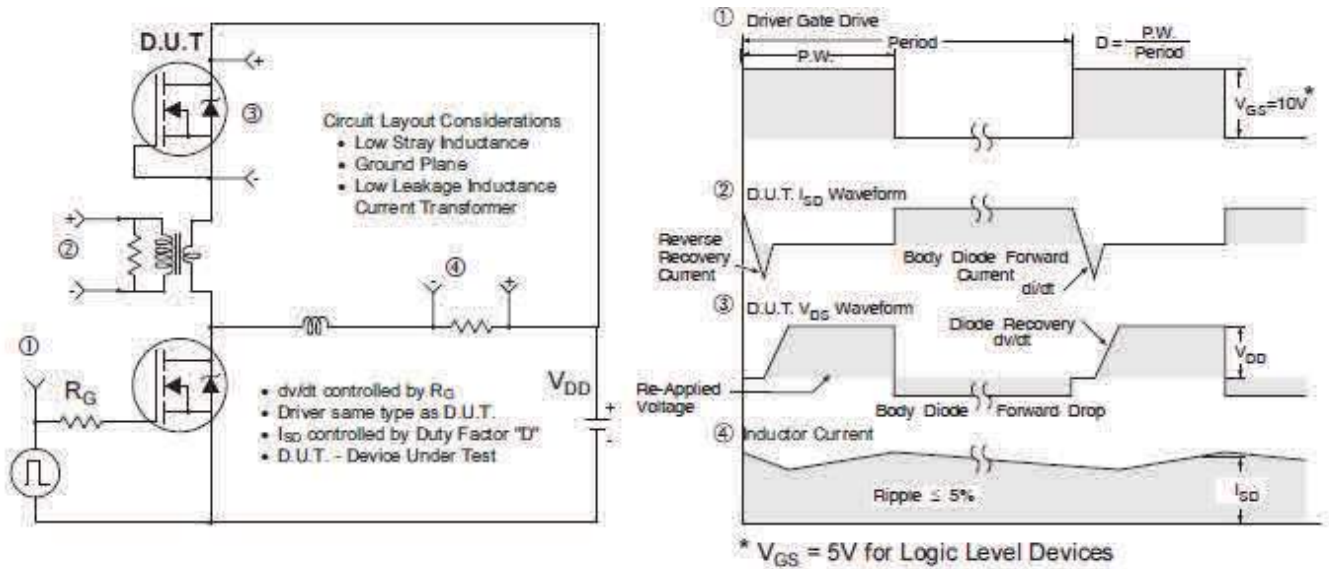
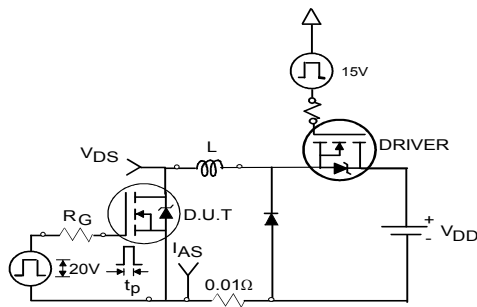
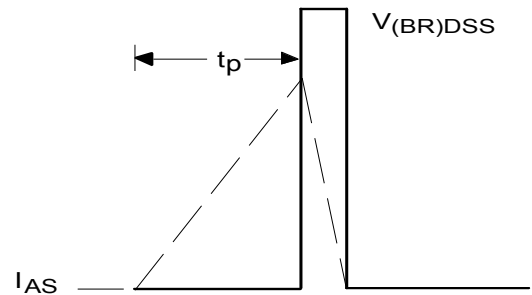
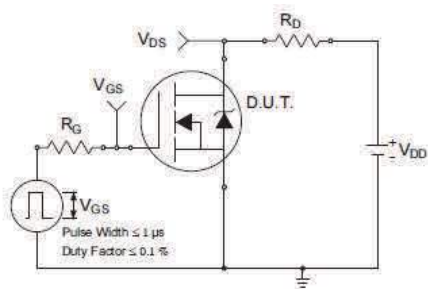
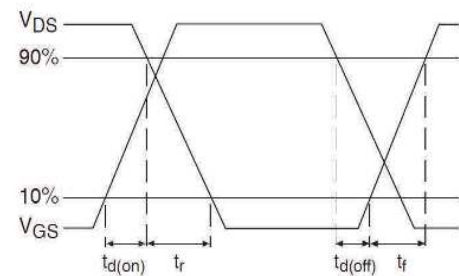
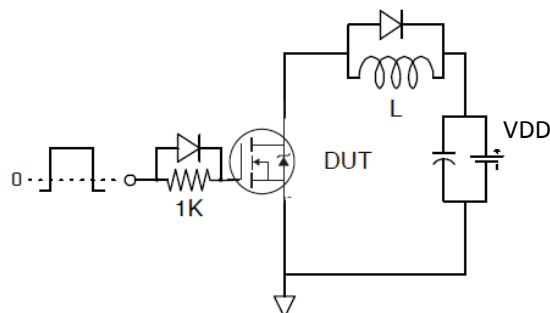
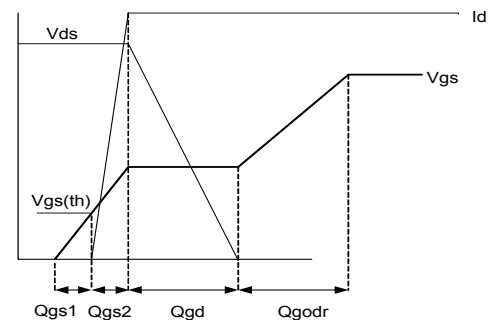

Fig 3. Typical Output Characteristics

Fig 4. Typical Output Characteristics

Fig 5. Typical Transfer Characteristics

Fig 6. Normalized On-Resistance vs. Temperature

Fig 7. Typical Capacitance vs. Drain-to-Source Voltage

Fig 8. Typical Gate Charge vs. Gate-to-Source Voltage

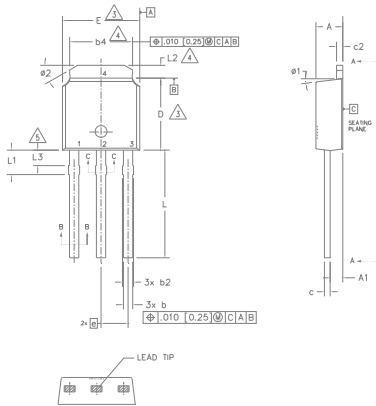

Fig 9. Typical Source-Drain Diode Forward Voltage

Fig 10. Maximum Safe Operating Area

Fig 11. Drain-to-Source Breakdown Voltage

Fig 12. Typical C_{oss} Stored Energy

Fig 13. Typical On-Resistance vs. Drain Current


Fig 14. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig 15. Avalanche Current vs. Pulse Width

Fig 16. Maximum Avalanche Energy vs. Temperature
**Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.irf.com)**

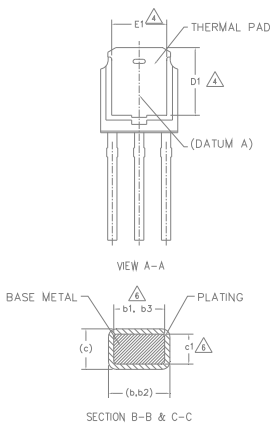
1. Avalanche failures assumption:
Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax} . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 23a, 23b.
4. $P_{D(ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
 t_{av} = Average time in avalanche.
 D = Duty cycle in avalanche = $t_{av} \cdot f$
 $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)
 $P_{D(ave)} = 1/2 (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$
 $I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$
 $E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$


Fig 17. Threshold Voltage vs. Temperature

Fig 18. Typical Recovery Current vs. di_F/dt

Fig 19. Typical Recovery Current vs. di_F/dt

Fig 20. Typical Stored Charge vs. di_F/dt

Fig 21. Typical Stored Charge vs. di_F/dt


Fig 22. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

Fig 23a. Unclamped Inductive Test Circuit

Fig 23b. Unclamped Inductive Waveforms

Fig 24a. Switching Time Test Circuit

Fig 24b. Switching Time Waveforms

Fig 25a. Gate Charge Test Circuit

Fig 25b. Gate Charge Waveform

I-Pak (TO-251AA) Package Outline (Dimensions are shown in millimeters (inches))


- NOTES:
- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS].
 - 3.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005 [0.13] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
 - 4.- THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
 - 5.- LEAD DIMENSION UNCONTROLLED IN L3.
 - 6.- DIMENSION b1, b3 & c1 APPLY TO BASE METAL ONLY.
 - 7.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA (Date 06/02).
 - 8.- CONTROLLING DIMENSION : INCHES.



SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1	0.89	1.14	.035	.045	
b	0.64	0.89	.025	.035	
b1	0.65	0.79	.025	.031	6
b2	0.76	1.14	.030	.045	
b3	0.76	1.04	.030	.041	6
b4	4.95	5.46	.195	.215	4
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	6
c2	0.46	0.89	.018	.035	
D	5.97	6.22	.235	.245	3
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	3
E1	4.32	-	.170	-	4
e	2.29 BSC		.090 BSC		
L	8.89	9.65	.350	.380	
L1	1.91	2.29	.045	.090	
L2	0.89	1.27	.035	.050	4
L3	0.89	1.52	.035	.060	5
phi1	0"	15"	0"	15"	
phi2	25"	35"	25"	35"	

LEAD ASSIGNMENTS
HEXFET

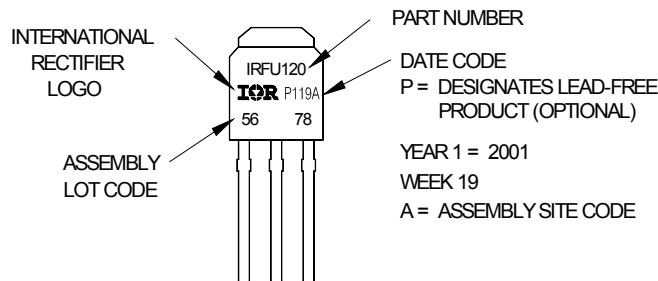
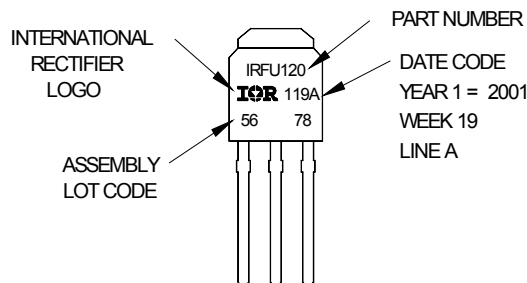
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

I-Pak (TO-251AA) Part Marking Information

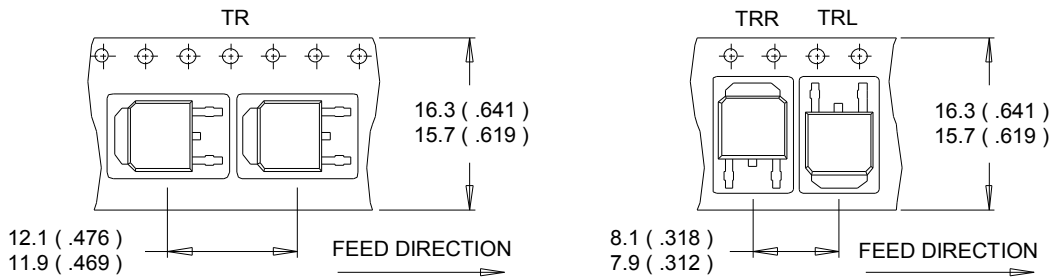
EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates Lead-Free"

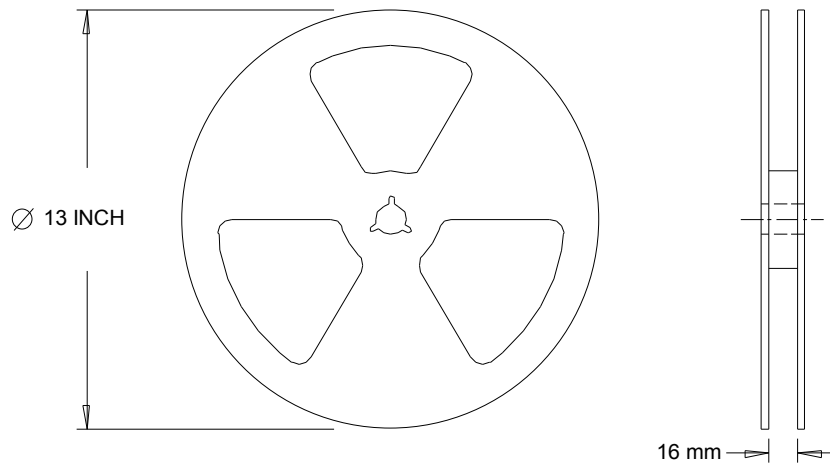
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

D-Pak (TO-252AA) Tape & Reel Information (Dimensions are shown in millimeters (inches))


- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial (per JEDEC JESD47F) ^{††}	
Moisture Sensitivity Level	D-Pak	MSL1
	I-Pak	
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability/>

†† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Comment
11/5/2014	<ul style="list-style-type: none"> • Updated $E_{AS(L=1mH)} = 242mJ$ on page 2 • Updated note 9 "Limited by T_{Jmax}, starting $T_J = 25^\circ C$, $L = 1mH$, $R_G = 50\Omega$, $I_{AS} = 22A$, $V_{GS} = 10V$" on page 2

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